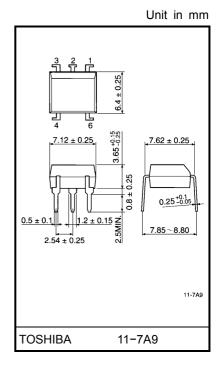
TOSHIBA Photocoupler GaAlAs Ired & Photo-Diode Array

TLP591B

Telecommunication
Programmable Controllers
MOS Gate Driver
MOS FET Gate Driver

The TOSHIBA TLP591B consists of an aluminum galium arsenide infrared emitting diode optically coupled to a series connected photo-diode array in a six lead plastic DIP package. TLP591B is suitable for MOS FET gate driver. TLP591B has an internal shunt resistor to optimize switching speed.

• UL recognized: UL1577, file no. E67349

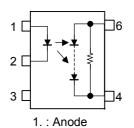


Maximum Ratings (Ta = 25°C)

	Characteristic	Symbol	Rating	Unit
	Forward current	l _F	50	mA
	Forward current derating (Ta ≥ 25°C)	ΔI _F /°C	-0.5	mA /°C
LED	Pulse forward current (100µs pulse, 100pps)	I _{FP}	1	Α
	Reverse voltage	V_{R}	3	V
	Junction temperature	Tj	125	°C
or	Forward current	I _{FD}	50	μA
Detector	Reverse voltage	V_{RD}	10	V
Ď	Junction temperature	Tj	125	°C
Storage temperature range		T _{stg}	-55~125	°C
Operating temperature range		T _{opr}	−40~85	°C
Lead soldering temperature (10 sec.)		T _{sol}	260	°C
Isolation voltage (AC, 1 min., R.H.≤ 60%) (Note 1)		BVS	2500	V _{rms}

(Note 1) Device considered a two terminal device: Pins 1, 2 and 3 shorted together, and pins 4 and 6 shorted together.

Pin Configuration (top view)



2. : Cathode 3. : NC

4. : Cathode 6. : Anode

2002-09-25

Recommended Operating Conditions

Characteristic	Symbol	Min.	Тур.	Max.	Unit
Forward current	I _F	_	20	25	mA
Operating temperature	T _{opr}	-25	_	85	°C

Individual Electrical Characteristics (Ta = 25°C)

	Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
	Forward voltage	V_{F}	I _F = 10 mA	1.2	1.4	1.7	V
LED	Reverse current	I _R	V _R = 3 V	_	_	10	μΑ
	Capacitance	C _T	V = 0, f = 1 MHz	_	30	60	pF
L	Forward voltage	V_{FD}	I _{FD} = 10 μA	_	7	_	V
Detector	Reverse current	I _{RD}	V _{RD} = 10 V	_	7	_	μΑ
	Capacitance (anode to cachode)	C _{TD}	V = 0, f = 1 MHz	_	_		pF

Coupled Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Open voltage	V _{OC}	I _F = 20 mA	7	8	_	V
Short Current	I _{SC}	I _F = 20 mA	24	40	_	μΑ

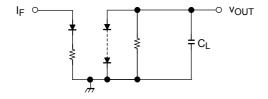
Isolation Characteristics (Ta = 25°C)

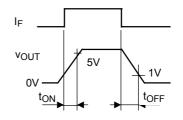
Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Capacitance (input to output)	Cs	V _S = 0, f = 1 MHz	_	8.0	_	pF
Isolation resistance	R _S	V _S = 500 V	5×10 ¹⁰	10 ¹⁴	_	
	BVS	AC, 1 minute	2500	_	_	Vrms
Isolation voltage		AC, 1 second, in oil	_	5000	_	VIIIIS
		DC, 1 minute, in oil	_	5000	_	Vdc

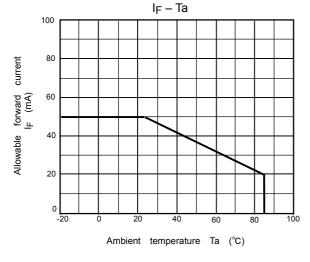
Switching Characteristics (Ta = 25°C)

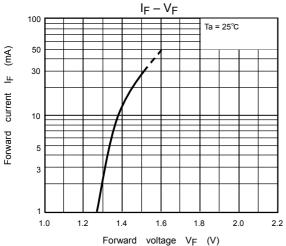
Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Turn-on time	t _{on}	I _F = 20 mA, C _L = 1000pF	_	0.2	_	ms
Turn-off time	t _{off}	(Fig. 1)	_	3	-	ms

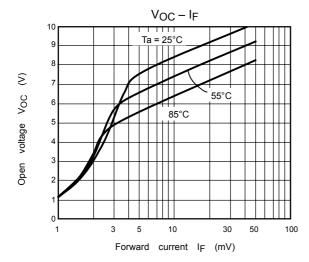
Fig. 1 Switching time test circuit

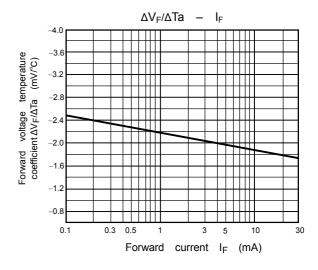


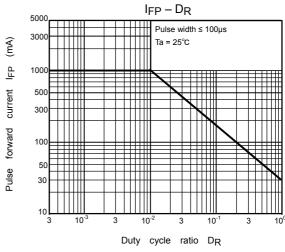


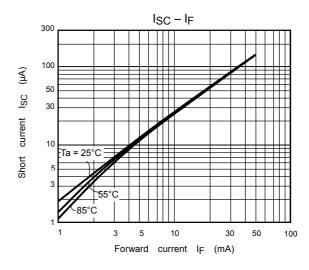












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